

## AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph extending from page 4, line 29 to page 5, line 9 as follows:

Thus, the invention is directed to a method for depositing ruthenium on a substrate, comprising exposing the substrate to a plasma which causes a high concentration of nucleation sites to be formed on the substrate, thus forming an exposed substrate; and depositing ruthenium on the exposed substrate by atomic layer deposition. The substrate is selected or may be selected from the group consisting of silicon dioxide, methyl silsesquioxane, hydrogen silsesquioxane, low dielectric constant materials, and high dielectric constant oxide substrates.

Please amend the paragraph on page 5, lines 11 to 19 as follows:

The plasma is or may be an oxygen plasma, and may be generated by passing molecular oxygen through a plasma generation source to produce activated radicals to thereby generate a large number of nucleation sites on the substrate. The plasma may also be a nitrogen and may be generated by passing molecular nitrogen through a plasma generation source to produce activated radicals to thereby generate a large number of nucleation sites on the substrate.

Please amend the paragraph on page 5, lines 29 to 30 as follows:

The ruthenium precursor is selected or may be selected from the group consisting of: